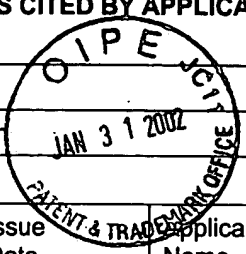


U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)					Doc. No. AMAT/5951		Serial No. 09/981,508	
LISTS OF PATENTS AND PUBLICATIONS CITED BY APPLICANT					Applicant Zheng, et al.			
(Use several sheets if necessary)					Filing Date October 16, 2001		Group Unknown	
Examiner Unknown								
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Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate	
UA.	A1	6,224,737	05/01/2001	Tsai, et al.	205	123	08/19/1999	
	A2	6,149,974	11/21/2000	Nguyen, et al.	427	255.29	05/05/1997	
	A3	6,133,619	10/17/2000	Sahota, et al.	257	649	08/31/1998	
	A4	6,071,814	06/06/2000	Jang	438	687	09/28/1998	
	A5	6,051,114	04/18/2000	Yao, et al.	204	192.3	06/23/1997	
	A6	6,048,445	04/11/2000	Brain	205	118	03/24/1998	
	A7	6,001,420	12/14/1999	Mosely, et al.	427	258	09/23/1996	
	A8	5,976,327	11/02/327	Tanaka	204	192.15	12/12/1997	
	A9	5,968,327	10/19/1999	Kobayashi et al.	204	298.11	02/12/1998	
	A10	5,966,634	10/12/1999	Imohara, et al.	438	687	03/25/1997	
	A11	5,933,753	08/03/1999	Simon, et al.	438	629	12/16/1996	
	A12	5,911,864	06/15/1999	Elridge	205	124	11/08/1996	
	A13	5,904,565	05/18/1999	Nguyen, et al.	438	687	07/17/1997	
	A14	5,863,392	01/26/1999	Drummond, et al.	204	192.12	05/05/1995	
	A15	5,858,184	01/12/1999	Fu, et al.	204	192.17	06/07/1995	
	A16	5,810,982	09/22/1998	Sellers	204	298.08	09/30/1996	
	A17	5,810,963	09/22/1998	Tomioka	156	345	09/27/1996	
UA.	A18	5,807,467	09/15/1998	Givens, et al.	204	192.12	01/22/1996	
Foreign Patent Documents								
Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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UA.	B1	0 892 428 A2	01/20/1999	EP	<del>H01L</del>	<del>21/768</del>	<input type="checkbox"/>	<input type="checkbox"/>
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UA.	C1	L. J. Kochel, "Pressure control of rf bias for sputtering", Rev. Sci. Instrm., Vol. 47, No. 12 (December 1976), pp.1555-1557						
	C2	Suzuki, et al., "Microwave plasma etching", Pergamon Press Ltd., Vol. 34, No. 10/11 (1984) pp. 953-957 *						
	C3	Rossnagel, et al., Collimated magnetron sputter deposition with grazing angle ion bombardment', J. Vac. Sci Tech, Vol. 13, No. 1 (Jan/Feb 1995), pp. 156 - 158						
Examiner <i>Wesley J. Lee</i>					Date Considered 7/22/03			
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\* No month avail.


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UA	A19	5,780,357	07/14/1998	Xu, et al.	438	639	06/02/1997
	A20	5,770,023	06/23/1998	Sellers	204	192.3	02/12/1996
	A21	5,759,906	06/02/1998	Lou	438	623	04/11/1997
	A22	5,744,376	04/28/1998	Chan, et al.	437	190	04/08/1996
	A23	5,731,245	03/24/1998	Joshi, et al.	438	705	10/28/1996
	A24	5,725,739	03/10/1998	Hu	204	192.3	07/08/1996
	A25	5,723,387	03/03/1998	Chen	438	692	07/22/1996
	A26	5,718,813	02/17/1998	Drummond, et al.	204	192.12	04/02/1993
	A27	5,693,563	12/02/1997	Teong	437	190	07/15/1996
	A28	5,662,788	09/02/1997	Sandhu, et al.	205	87	06/03/1996
	A29	5,651,865	07/29/1997	Sellers	204	192.13	06/17/1994
	A30	5,639,357	06/17/1997	Xu	204	192.3	05/12/1994
	A31	5,612,254	03/18/1997	Mu, et al.	437	195	06/29/1992
	A32	5,585,974	12/17/1996	Shrinkle	360	46	02/17/1995
UA	A33	5,585,673	12/17/1996	Joshi, et al.	257	751	11/22/1994
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Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation
UA	B2	0 798 778 A2	10/01/1997	EP	<del>H04L</del>	<del>21768</del>	YES <input checked="" type="checkbox"/> NO <input type="checkbox"/>
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Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.					
UA	C4	Yasui, et al., "Electron cyclotron resonance plasma generation using a planar ring-cusp magnetic field and reentrant coaxial cavity", J. Vac. Sci. Tech., Vol. 13, No. 4 (July/August 1995), pp. 2105-2109					
	C5	Holber, et al., "Copper deposition by electron cyclotron resonance plasma", J. Vac. Sci. Tech., Vol. 11, No. 6 (Nov/Dec 1993), pp. 2903 - 2910					
	C6	Cheng, et al., "Directional deposition of Cu into semiconductor trench structures using ionized magnetron sputtering", J. Vac. Sci. Tech., Vol 13, No. 2 (Mar/Apr 1995), pp. 203-208					
UA	C7	P. Kidd, "A Magnetically confined and electron cyclotron resonance heated plasma machine for coating and ion surface modification use", J. Vac. Sci. Tech., Vol. 9, No. 3 (May/Jun 1991), pp. 466-473					
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U.S. Patent Documents							
Examiner Initial		Document Number	Date	Applicant(s) Name	Class	Subclass	Filing Date if Appropriate
UW	A34	5,584,974	12/17/1996	Sellers	204	192.13	10/20/1995
	A35	5,510,011	04/23/1996	Okamura, et al.	204	192.3	12/22/1994
	A36	5,486,492	01/23/1996	Yamamoto, et al.	437	192	10/29/1993
	A37	5,376,584	12/27/1994	Agarwala	437	183	12/31/1992
	A38	5,346,600	09/13/1994	Nieh, et al.	204	192.3	08/14/1992
	A39	5,303,139	04/12/1994	Mark	363	63	07/30/1992
	A40	5,302,266	04/12/1994	Grabarz, et al.	204	192.12	09/25/1992
	A41	5,262,354	11/16/1993	Cote, et al.	437	195	02/26/1992
	A42	5,256,274	10/26/1993	Poris	205	123	11/22/1991
	A43	5,126,028	06/30/1992	Hurwitt, et al.	204	192.13	08/22/1990
UW	A44	5,078,847	01/07/1992	Grosman, et al.	204	192.31	08/29/1990
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Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation
UW	B3	0 788 160 A3	06/16/1999	EP	H04L	23/522	YES <input type="checkbox"/> NO <input type="checkbox"/>
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UW	C8	M. Yamashita, "Fundamental characteristics of built-in high-frequency coil-type sputtering apparatus", <i>J. Vac. Sci. Tech.</i> , 7(2) (Mar/Apr 1989), pp.151-158					
	C9	S. Samukawa, "Wave propagation and plasma uniformity in an electron cyclotron resonance plasma", <i>J. Vac. Sci. Tech.</i> , 11(5) (Sep/Oct 1993), pp. 2572-2576					
	C10	Apblett, et al., "Silicon nitride growth in a high-density plasma system", <i>Solid State Tech.</i> , (Nov. 1995), pp.73-74 & 78 and 80					
	C11	Suzuki, et al., "Microwave Plasma Etching". <i>J. App. Phys.</i> , 16(11) (Nov. 1977), pp.1979-1984					
	C12	Getty, et al., "Size-scalable 2.45 GHz electron cyclotron resonance plasma source using permanent magnets and waveguide coupling", <i>J. Vac. Sci. Tech.</i> , 12(1) (Jan/Feb 1994), pp. 408-415					
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UW.	A45	4,999,096	03/12/1991	Nihei, et al.	204	192.3	06/29/1988	
	A46	4,963,239	10/16/1990	Shimamura, et al.	204	192.12	01/26/1989	
	A47	4,874,494	10/17/1989	Ohmi	204	192.12	06/06/1987	
	A48	4,874,493	10/17/1989	Pan	204	192.11	03/28/1988	
	A49	4,865,712	09/12/1989	Mintz	204	298	07/28/1987	
	A50	4,756,801	07/12/1988	Jokinen, et al.	162	175	10/24/1986	
UW.	A51	3,410,774	11/12/1968	Barson, et al.	204	192	10/23/1965	
	A52	09/360,883		Paterson, et al.			07/23/1999	
	A53	08/768,058		Ramaswami, et al.			12/16/1996	
	A54	09/449,202		Gopalraja			11/24/1999	
	A55	09/454,355		Forster			12/03/1999	
	A56	09/219,187		Sivaramakrishnan et al.			12/21/1998	
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UW.	B4	0 297 502 A2	06/28/1988	EP	C23C	14/34	<input type="checkbox"/>	<input type="checkbox"/>
UW.	B5	0 123 456 A2	10/31/1984	EP	H04N	7/12	<input type="checkbox"/>	<input type="checkbox"/>
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UW.	C14	"Endpoint Detection method for Ion Etching of a Material Having a titanium Nitride Underlayer", Research Disclosure, February 1991, No. 322, Kenneth Mason Publications Ltd, England						
	C15	Novellus Damascus Home Page, "12 Steps of Damascus" **						
	C16	S. Matsuo, "Reactive ion-beam etching and plasma deposition techniques using electron cyclotron resonance plasma," <i>Appl. Sol. State Sci</i> , Academic Press (1985), pp. 75-117 *						
	C17	Gorbatkin, et al., "Cu metallization using a permanent magnet electron cyclotron resonance microwave plasma sputtering hybrid system", <i>J. Vac. Sci. Tech</i> , 14(3) (May/Jun 1996), pp.1853-1859						
	C18	Park, et al., "A novel A-1 reflow process using surface modification by the ECR plasma treatment and its application to the 256Mbit DRAM, <i>IEDM 94</i> , 109-112, pp.5.4.1 - 5.5.5 (1994) *						
UW.	C19	Koenig, et al., "RF sputtering system with a variable substrate bias, <i>IBM Tech, Discl. Bull</i> 13(2) (July 1970), pp. 323-324						
Examiner UW.					Date Considered 7/22/03			
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\*\* No Date Avail

\* No month Avail

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>				Applicant Zheng et al.		Confirmation No. 6901	
(Use several sheets if necessary)				Filing Date October 16, 2001		Group 2811	
Examiner      Unknown							
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*Examiner Initial	Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
LM	A1	6,432,821	Dubin et al.	438	678	12-18-2000
	A2					
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<b>Foreign Patent Documents</b>							
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<b>OTHER ART</b>	
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	C1
	C2
	C3

Examiner <i>Wesley A. 102</i>	Date Considered <i>7/22/03</i>
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